

# NSL12AWT1G

## High Current Surface Mount PNP Silicon Low $V_{CE(sat)}$ Transistor for Battery Operated Applications

### Features

- High Current Capability (3 A)
- High Power Handling (Up to 650 mW)
- Low  $V_{CE(s)}$  (170 mV Typical @ 1 A)
- Small Size
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

### Benefits

- High Specific Current and Power Capability Reduces Required PCB Area
- Reduced Parasitic Losses Increases Battery Life

### MAXIMUM RATINGS ( $T_A = 25^\circ\text{C}$ )

Rating	Symbol	Max	Unit
Collector-Emitter Voltage	$V_{CEO}$	-12	Vdc
Collector-Base Voltage	$V_{CBO}$	-12	Vdc
Emitter-Base Voltage	$V_{EBO}$	-5.0	Vdc
Collector Current – Continuous – Peak	$I_C$ $I_{CM}$	-2.0 -3.0	Adc
Electrostatic Discharge	ESD	HBM Class 3 MM Class C	

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

### THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation $T_A = 25^\circ\text{C}$ Derate above $25^\circ\text{C}$	$P_D$ (Note 1)	450 3.6	mW mW/ $^\circ\text{C}$
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$ (Note 1)	275	$^\circ\text{C}/\text{W}$
Total Device Dissipation $T_A = 25^\circ\text{C}$ Derate above $25^\circ\text{C}$	$P_D$ (Note 2)	650 5.2	mW mW/ $^\circ\text{C}$
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$ (Note 2)	192	$^\circ\text{C}/\text{W}$
Thermal Resistance, Junction-to-Lead 6	$R_{\theta JL}$	105	$^\circ\text{C}/\text{W}$
Total Device Dissipation (Single Pulse < 10 sec.)	$P_D$ Single	1.4	W
Junction and Storage Temperature Range	$T_J, T_{stg}$	-55 to +150	$^\circ\text{C}$

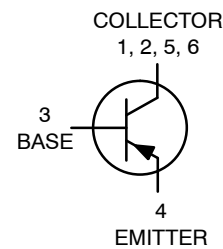
1. FR-4, Minimum Pad, 1 oz Coverage
2. FR-4, 1" Pad, 1 oz Coverage



ON Semiconductor®

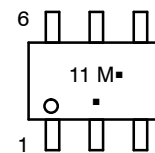
<http://onsemi.com>

**12 VOLTS**  
**3.0 AMPS**  
**PNP TRANSISTOR**



**SC-88/SOT-363**  
**CASE 419B**  
**STYLE 20**

### MARKING DIAGRAM



M = Date Code  
▪ = Pb-Free Package  
(Note: Microdot may be in either location)

### ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 2 of this data sheet.

# NSL12AWT1G

## ELECTRICAL CHARACTERISTICS ( $T_J = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
<b>OFF CHARACTERISTICS</b>					
Collector–Emitter Breakdown Voltage, ( $I_C = -10\text{ mAdc}$ , $I_B = 0$ )	$V_{(BR)CEO}$	-12	-15	-	Vdc
Collector–Base Breakdown Voltage, ( $I_C = -0.1\text{ mAdc}$ , $I_E = 0$ )	$V_{(BR)CBO}$	-12	-25	-	Vdc
Emitter–Base Breakdown Voltage, ( $I_E = -0.1\text{ mAdc}$ , $I_C = 0$ )	$V_{(BR)EBO}$	-5.0	-7.0	-	Vdc
Collector Cutoff Current, ( $V_{CB} = -12\text{ Vdc}$ , $I_E = 0$ )	$I_{CBO}$	-	-0.02	-0.1	$\mu\text{Adc}$
Collector–Emitter Cutoff Current, ( $V_{CES} = -12\text{ Vdc}$ , $I_E = 0$ )	$I_{CES}$	-	-0.03	-0.1	$\mu\text{Adc}$
Emitter Cutoff Current, ( $V_{CES} = -5.0\text{ Vdc}$ , $I_E = 0$ )	$I_{EBO}$	-	-0.03	-0.1	$\mu\text{Adc}$

## ON CHARACTERISTICS

DC Current Gain (Note 3) ( $I_C = -0.5\text{ A}$ , $V_{CE} = -1.5\text{ V}$ ) ( $I_C = -0.8\text{ A}$ , $V_{CE} = -1.5\text{ V}$ ) ( $I_C = -1.0\text{ A}$ , $V_{CE} = -1.5\text{ V}$ )	$h_{FE}$	100 100 100	180 165 160	- 300 -	
Collector–Emitter Saturation Voltage (Note 3) ( $I_C = -0.5\text{ A}$ , $I_B = -10\text{ mA}$ ) ( $I_C = -0.8\text{ A}$ , $I_B = -16\text{ mA}$ ) ( $I_C = -1.0\text{ A}$ , $I_B = -20\text{ mA}$ )	$V_{CE(sat)}$	-	-0.10 -0.14 -0.17	-0.160 -0.235 -0.290	V
Base–Emitter Saturation Voltage (Note 3) ( $I_C = -1.0\text{ A}$ , $I_B = -20\text{ mA}$ )	$V_{BE(sat)}$	-	-0.84	-0.95	V
Base–Emitter Turn–on Voltage (Note 3) ( $I_C = -1.0\text{ A}$ , $V_{CE} = -1.5\text{ V}$ )	$V_{BE(on)}$	-	-0.81	-0.95	V
Cutoff Frequency ( $I_C = -100\text{ mA}$ , $V_{CE} = -5.0\text{ V}$ , $f = 100\text{ MHz}$ )	$f_T$	-	100	-	MHz
Output Capacitance ( $V_{CB} = -1.5\text{ V}$ , $f = 1.0\text{ MHz}$ )	$C_{obo}$	-	50	65	pF

3. Pulsed Condition: Pulse Width < 300  $\mu\text{sec}$ , Duty Cycle < 2%

## ORDERING INFORMATION

Device	Package	Shipping <sup>†</sup>
NSL12AWT1G	SOT-363 (Pb-Free)	3000 Tape & Reel

<sup>†</sup>For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

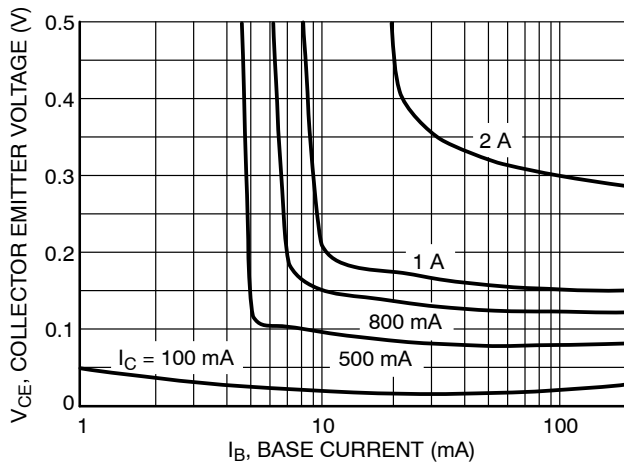


Figure 1. Collector Emitter Voltage vs Base Current

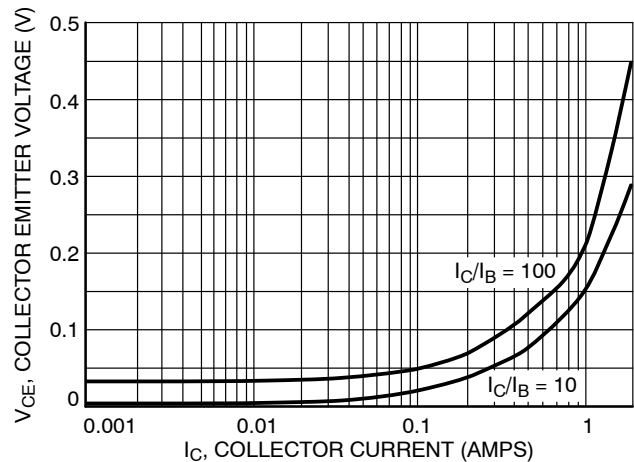
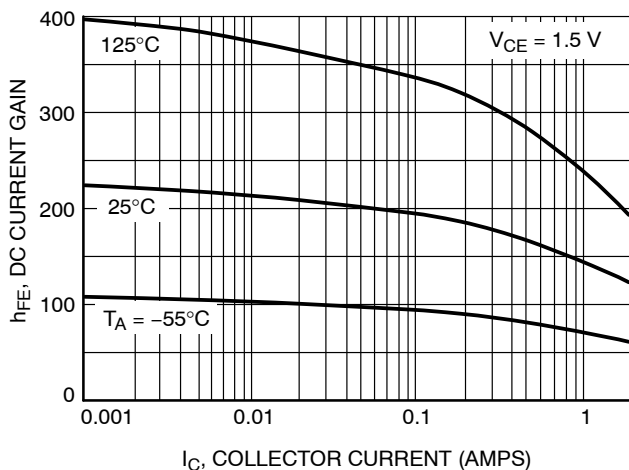
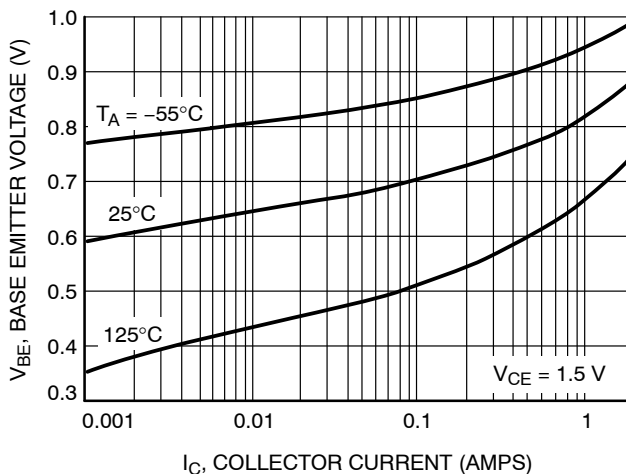


Figure 2. Collector Emitter Voltage vs Collector Current

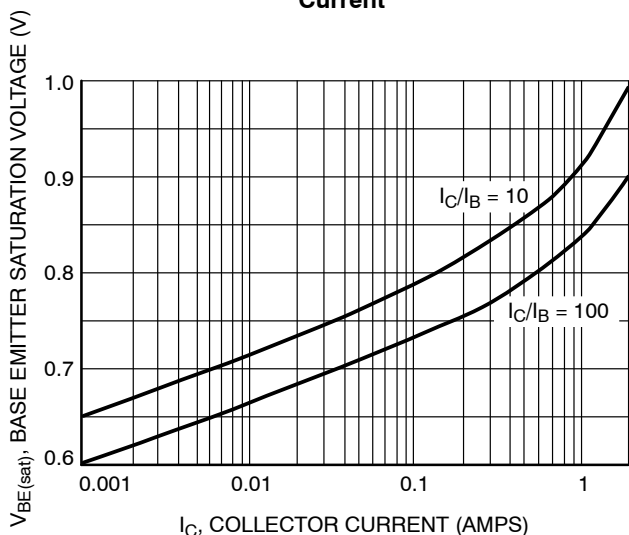
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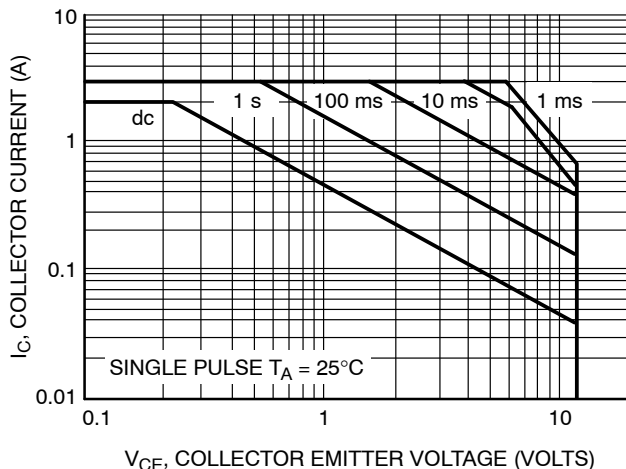
**Figure 3. DC Current Gain versus Collector Current**



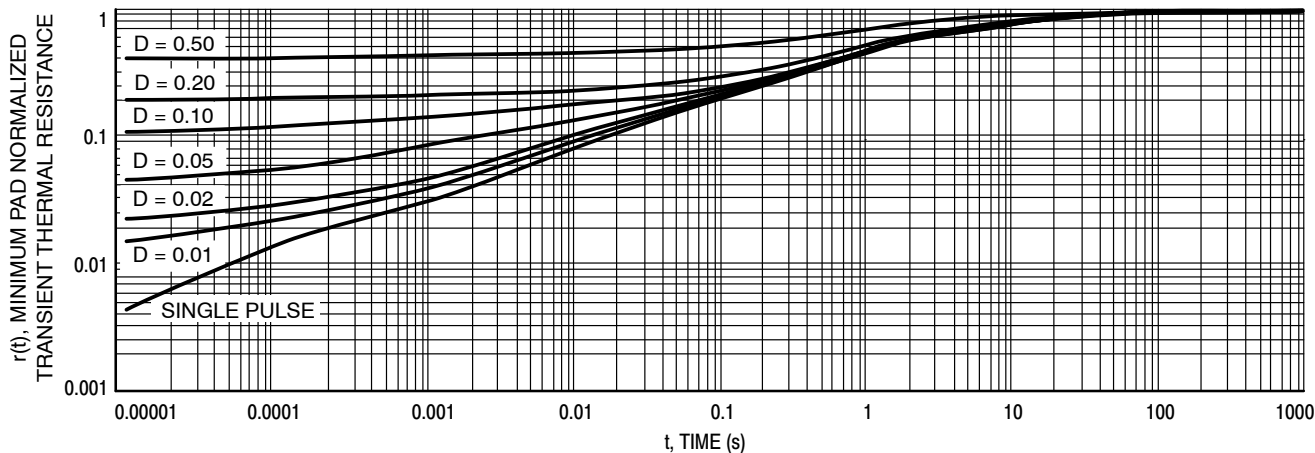
**Figure 4. Base Emitter Voltage versus Collector Current**



**Figure 5. Base Emitter Saturation Voltage versus Base Current**



**Figure 6. Safe Operating Area**



**Figure 7. Normalized Thermal Response**

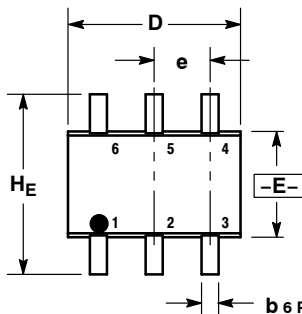
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## PACKAGE DIMENSIONS

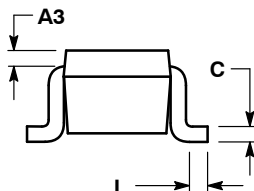
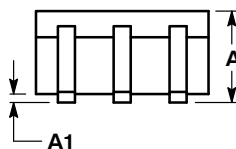
SC-88/SC70-6/SOT-363  
CASE 419B-02  
ISSUE W

NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. 419B-01 OBSOLETE, NEW STANDARD 419B-02.



b 6 PL  
⊕ 0.2 (0.008) M E M

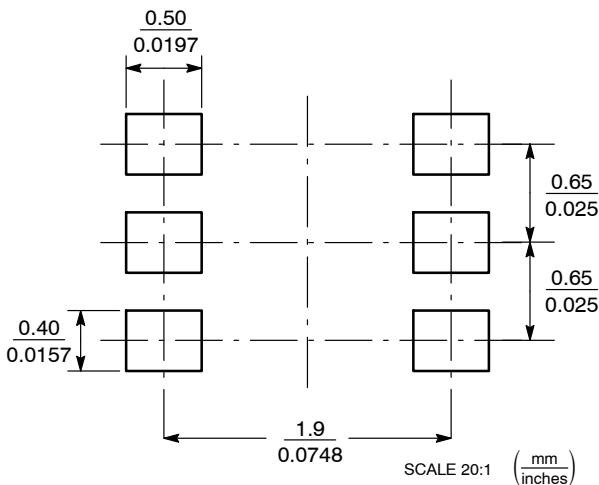


DIM	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	0.80	0.95	1.10	0.031	0.037	0.043
A1	0.00	0.05	0.10	0.000	0.002	0.004
A3	0.20 REF			0.008 REF		
b	0.10	0.21	0.30	0.004	0.008	0.012
C	0.10	0.14	0.25	0.004	0.005	0.010
D	1.80	2.00	2.20	0.070	0.078	0.086
E	1.15	1.25	1.35	0.045	0.049	0.053
e	0.65 BSC			0.026 BSC		
L	0.10	0.20	0.30	0.004	0.008	0.012
HE	2.00	2.10	2.20	0.078	0.082	0.086

STYLE 20:

- PIN 1. COLLECTOR  
2. COLLECTOR  
3. BASE  
4. EMITTER  
5. COLLECTOR  
6. COLLECTOR

### SOLDERING FOOTPRINT\*



\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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